

	Type	L #	Hits	Search Text	DBs
1	IS&R	L1	1	("6399971").PN.	USPAT
2	BRS	L2	1	("5481120").PN.	US- PGPUB; USPAT; USOCR
3	BRS	L3	5	(base adj contact) with (GaInAsSb or InGaAsSb or GaInSbAs or InGaSbAs or (Ga near4 Sb near4 As))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	Hits	Search Text
1	BRS	158	((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)
2	IS&R	1649	(438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.
3	BRS	52	((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.)
4	IS&R	2	("6399971").PN.
5	BRS	1	"6399971".URPN.
6	BRS	1	"5481120".PN.
7	BRS	2	jp-05326546-\$.did.
8	BRS	0	jp-08-335588-\$.did.
9	BRS	2	jp-05326546-\$.did. jp-08335588-\$.did. jp-07015357-\$.did.
10	BRS	1	jp-08335588-\$.did.
11	BRS	2	jp-07015357-\$.did.
12	BRS	0	jp-0715357-\$.did.
13	BRS	0	jp-70015357-\$.did.
14	BRS	482	(carbon c) near4 (dope doping doped) with base

	<b>DBs</b>
<b>1</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>2</b>	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
<b>3</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>4</b>	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
<b>5</b>	USPAT
<b>6</b>	USPAT
<b>7</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>8</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>9</b>	JPO
<b>10</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>11</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>12</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>13</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>14</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text
15	BRS	11	((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.) and ((carbon c) near4 (dope doping doped) with base)
16	BRS	745	(carbon c) near4 (dope doping doped implant\$5) with base
17	BRS	745	(carbon c) near4 (dope doping doped implant\$5) with base
18	BRS	12	((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.) and ((carbon c) near4 (dope doping doped implant\$5) with base)
19	BRS	1	((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.) and ((carbon c) near4 (dope doping doped implant\$5) with base)) not (((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.) and ((carbon c) near4 (dope doping doped) with base))
20	IS&R	1649	(438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.

	<b>DBs</b>
<b>15</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>16</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>17</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>18</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>19</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>20</b>	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text
21	BRS	1238129	(gallium indium ga in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" gaassb gasbas "ga as sb" "ga sb as" inassb insbas "in as sb" "in sb as" gainas gainsb ingaas ingasb "ga in as" "ga in sb" "in ga as" "in ga sb") and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.)
22	BRS	1003	((gallium indium ga in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" gaassb gasbas "ga as sb" "ga sb as" inassb insbas "in as sb" "in sb as" gainas gainsb ingaas ingasb "ga in as" "ga in sb" "in ga as" "in ga sb")) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.)
23	BRS	1002	((gallium indium ga in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb" "in sb as" gainas ingaas "ga in as" "in ga as")) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.)
24	BRS	37	((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)) and (((gallium indium ga in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb" "in sb as" gainas ingaas "ga in as" "in ga as")) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.))

	<b>DBs</b>
<b>21</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>22</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>23</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>24</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text
25	BRS	94	(base and emitter and base with (contact and electrode)) and (((gallium indium ga in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb" "in sb as" gainas ingaas "ga in as" "in ga as")) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.))
26	BRS	57	((base and emitter and base with (contact and electrode)) and (((gallium indium ga in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb" "in sb as" gainas ingaas "ga in as" "in ga as")) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.))) not (((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)) and (((gallium indium ga in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb" "in sb as" gainas ingaas "ga in as" "in ga as")) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.)))
27	BRS	1443	(base and emitter and base near (contact and electrode))
28	BRS	193	(base and emitter and base near (contact and electrode)) and base with ((gallium indium ga in) with (arsenic antimony as sb) (gainassb "ga in as sb" ingaassb ingasbas gainsbas "in ga as sb" "in ga sb as" "ga in sb as" inassb insbas "in as sb" "in sb as" gainas ingaas "ga in as" "in ga as"))
29	BRS	25	(heat\$3 anneal\$4) with base with remov\$3 near (hydrogen "h.sub.2")



	DBs
25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
27	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
28	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
29	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text
30	BRS	26	(heat\$3 anneal\$4) with base with (eliminate remov\$3) near (hydrogen "h.sub.2")
31	BRS	13	((heat\$3 anneal\$4) with base with' (eliminate remov\$3) near (hydrogen "h.sub.2")) and ("438"/\$6 "257"/\$6)
32	BRS	1153	lattice near (matched matching matches match) with (MBE MOMBE epitaxial epitaxy)
33	BRS	645	(lattice near (matched matching matches match) with (MBE MOMBE epitaxial epitaxy)) and ("438"/\$6 "257"/\$6)
34	IS&R	1649	(438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.
35	BRS	58	((lattice near (matched matching matches match) with (MBE MOMBE epitaxial epitaxy)) and ("438"/\$6 "257"/\$6)) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.)
36	BRS	33	emitter with ((INP "in p") with (algaas gaalas "al ga as" "ga al as"))
37	BRS	21	base with (eliminate remov\$3) near (hydrogen "h.sub.2") and ("438"/\$6 "257"/\$6)
38	BRS	13	(US-5846869-\$ or US-6031255-\$ or US-6258685-\$ or US-6432788-\$ or US-6451659-\$ or US-6455390-\$ or US-6537838-\$ or US-4047976-\$ or US-5693541-\$).did. or (US-20010026971-\$ or US-20020031892-\$ or US-20020058399-\$ or US-20020187568-\$).did.
39	BRS	8	( base with (eliminate remov\$3) near (hydrogen "h.sub.2") and ("438"/\$6 "257"/\$6)) not ((US-5846869-\$ or US-6031255-\$ or US-6258685-\$ or US-6432788-\$ or US-6451659-\$ or US-6455390-\$ or US-6537838-\$ or US-4047976-\$ or US-5693541-\$).did. or (US-20010026971-\$ or US-20020031892-\$ or US-20020058399-\$ or US-20020187568-\$).did.)
40	IS&R	2	("20020090789").PN.

	<b>DBs</b>
<b>30</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>31</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>32</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>33</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>34</b>	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
<b>35</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>36</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>37</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>38</b>	US-PGPUB; USPAT
<b>39</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>40</b>	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text
41	IS&R	2	("5846869").PN.
42	IS&R	2	("5903018").PN.
43	BRS	1039098	((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.) nd @pd>="20031013"
44	BRS	5	((lattice near (matched matching matches match) with (MBE MOMBE epitaxial epitaxy)) and ("438"/\$6 "257"/\$6)) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.) and @pd>="20031013"
45	BRS	9	((heterojunction hetero) with (bipolar bi near polar) with (transistor) hbt hbts) and base and emitter with mesa and base with (contact and electrode)) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.) and @pd>="20031013"
46	IS&R	2	("20020090789").PN. /
47	BRS	8963	InP near substrate
48	BRS	199	InP near emitter
49	BRS	145	(InP near substrate) and (InP near emitter)
50	BRS	6	InP near3 AlGaAs near3 emitter
51	BRS	4	(InP near substrate) and (InP near3 AlGaAs near3 emitter)
52	IS&R	2	("5903018").PN.

	<b>DBs</b>
<b>41</b>	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
<b>42</b>	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
<b>43</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>44</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>45</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>46</b>	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
<b>47</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>48</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>49</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>50</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>51</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>52</b>	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text
53	BRS	4	((lattice near (matched matching matches match) with (MBE MOMBE epitaxial epitaxy))) and ((438/47,94,172,191,235,312,313,314,315,317,320,for.286).CCLS.) and @pd>="20040504"
54	BRS	1	10/604981

	<b>DBs</b>
<b>53</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
<b>54</b>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB